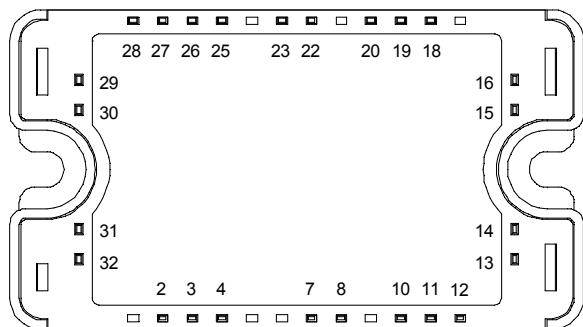
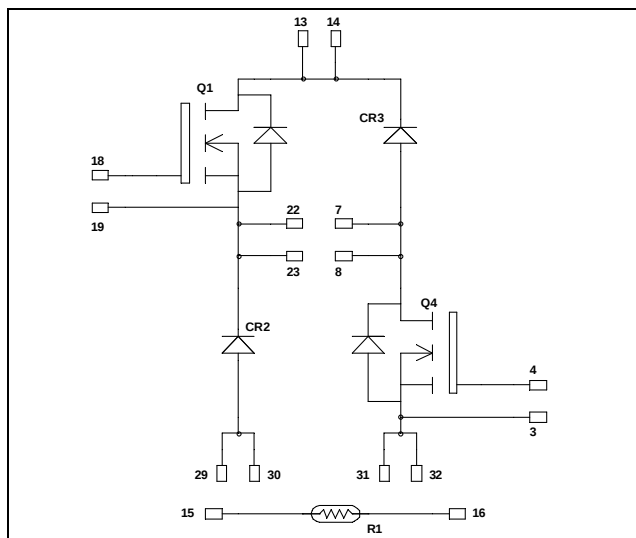


Asymmetrical bridge Super Junction MOSFET Power Module

$$V_{DSS} = 600V$$

$$R_{DSon} = 35m\Omega \text{ max @ } T_j = 25^\circ C$$

$$I_D = 72A \text{ @ } T_c = 25^\circ C$$



All multiple inputs and outputs must be shorted together
 Example: 13/14 ; 29/30 ; 22/23 ...

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

Features

- **COOLMOS** Power Semiconductors
 - Ultra low R_{DSon}
 - Low Miller capacitance
 - Ultra low gate charge
 - Avalanche energy rated
 - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
 - Symmetrical design
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{DSS}	Drain - Source Breakdown Voltage	600	V
I_D	Continuous Drain Current	$T_c = 25^\circ C$	72
		$T_c = 80^\circ C$	54
I_{DM}	Pulsed Drain current	200	A
V_{GS}	Gate - Source Voltage	± 20	V
R_{DSon}	Drain - Source ON Resistance	35	m Ω
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	416
I_{AR}	Avalanche current (repetitive and non repetitive)	20	A
E_{AR}	Repetitive Avalanche Energy	1	mJ
E_{AS}	Single Pulse Avalanche Energy	1800	



CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 600V$ $T_j = 25^\circ\text{C}$			40	μA
		$V_{GS} = 0V, V_{DS} = 600V$ $T_j = 125^\circ\text{C}$			375	
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 72A$			35	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 5.4\text{mA}$	2.1	3	3.9	V
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 150	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0V$		14		nF
C_{oss}	Output Capacitance	$V_{DS} = 25V$		5.13		
C_{rss}	Reverse Transfer Capacitance	$f = 1\text{MHz}$		0.42		
Q_g	Total gate Charge	$V_{GS} = 10V$		518		nC
Q_{gs}	Gate – Source Charge	$V_{Bus} = 300V$		58		
Q_{gd}	Gate – Drain Charge	$I_D = 72A$		222		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching @ 125°C $V_{GS} = 15V$ $V_{Bus} = 400V$ $I_D = 72A$ $R_G = 2.5\Omega$		21		ns
T_r	Rise Time			30		
$T_{d(off)}$	Turn-off Delay Time			283		
T_f	Fall Time			84		
E_{on}	Turn-on Switching Energy	Inductive switching @ 25°C $V_{GS} = 15V, V_{Bus} = 400V$ $I_D = 72A, R_G = 2.5\Omega$		1340		μJ
E_{off}	Turn-off Switching Energy			1960		
E_{on}	Turn-on Switching Energy	Inductive switching @ 125°C $V_{GS} = 15V, V_{Bus} = 400V$ $I_D = 72A, R_G = 2.5\Omega$		2192		μJ
E_{off}	Turn-off Switching Energy			2412		

Diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		600			V
I_{RM}	Maximum Reverse Leakage Current	$V_R = 600V$	$T_j = 25^\circ\text{C}$		25	μA
			$T_j = 125^\circ\text{C}$		500	
I_F	DC Forward Current	$T_c = 80^\circ\text{C}$		60		A
V_F	Diode Forward Voltage	$I_F = 60A$	$T_j = 25^\circ\text{C}$	1.7	2.3	V
		$I_F = 120A$		2		
		$I_F = 60A$	$T_j = 125^\circ\text{C}$	1.4		
t_{rr}	Reverse Recovery Time	$I_F = 60A$ $V_R = 400V$ $di/dt = 200A/\mu s$	$T_j = 25^\circ\text{C}$	70		ns
			$T_j = 125^\circ\text{C}$	140		
Q_{rr}	Reverse Recovery Charge	$I_F = 60A$ $V_R = 400V$ $di/dt = 200A/\mu s$	$T_j = 25^\circ\text{C}$	100		nC
			$T_j = 125^\circ\text{C}$	690		

Thermal and package characteristics

Symbol	Characteristic	Min	Typ	Max	Unit
R _{thJC}	Junction to Case Thermal Resistance	CoolMOS		0.30	°C/W
		diode		0.85	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t=1 min, I _{isol} <1mA, 50/60Hz	4000			V
T _J	Operating junction temperature range	-40		150	°C
T _{STG}	Storage Temperature Range	-40		125	
T _C	Operating Case Temperature	-40		100	
Torque	Mounting torque	To heatsink	M4	2.5	N.m
Wt	Package Weight			110	g

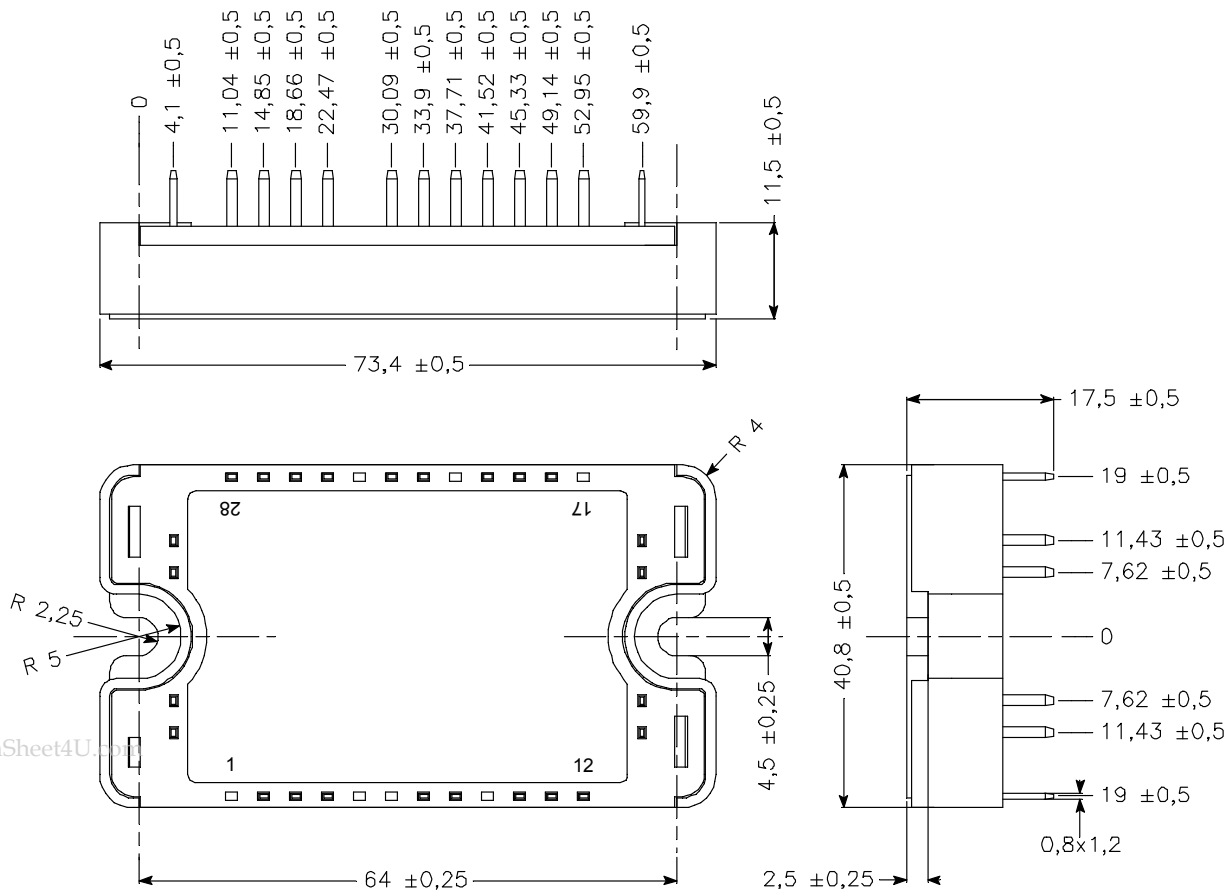
Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
ΔR ₂₅ /R ₂₅			5		%
B _{25/85}	T ₂₅ = 298.15 K		3952		K
ΔB/B	T _C = 100°C		4		%

$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

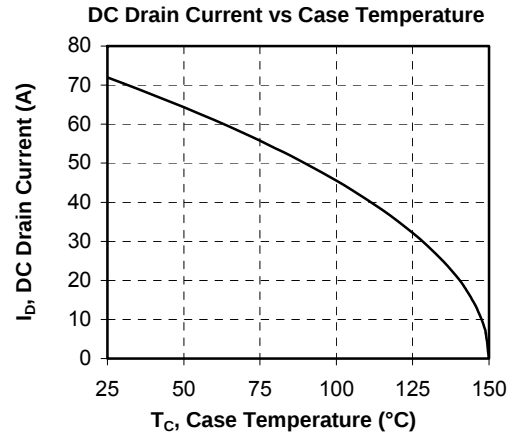
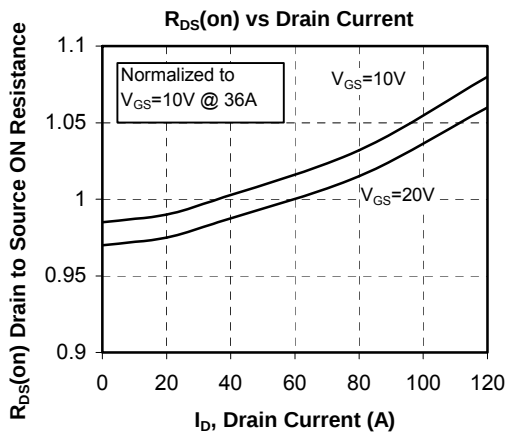
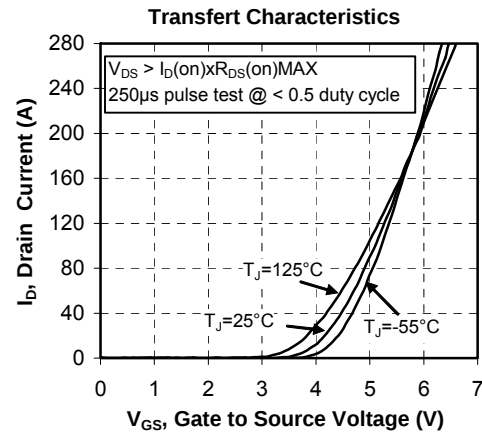
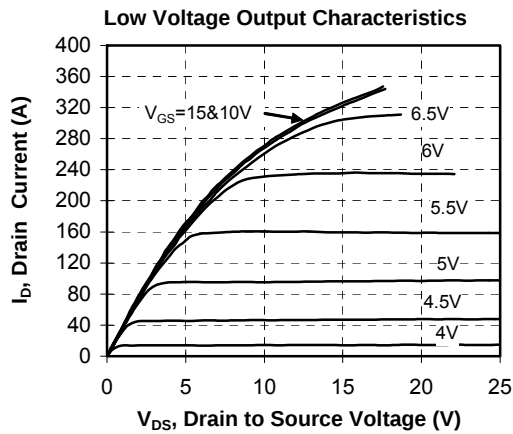
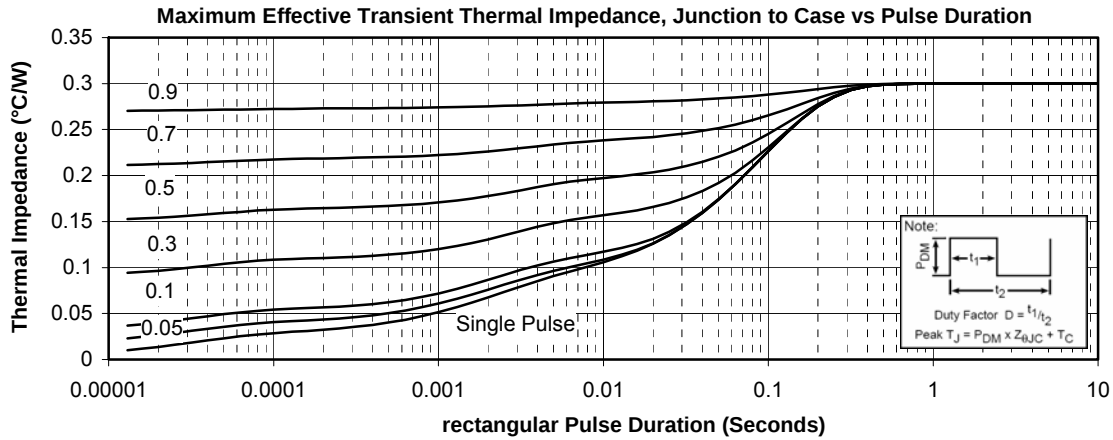
T: Thermistor temperature
 R_T: Thermistor value at T

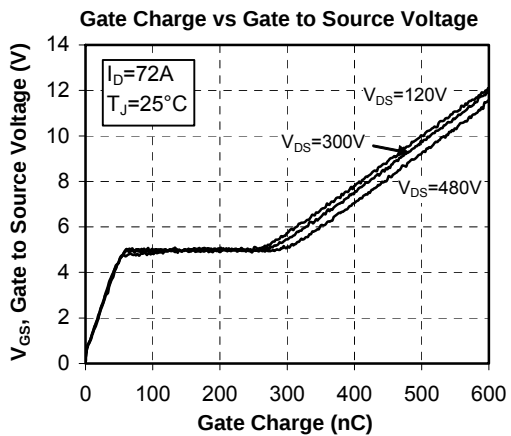
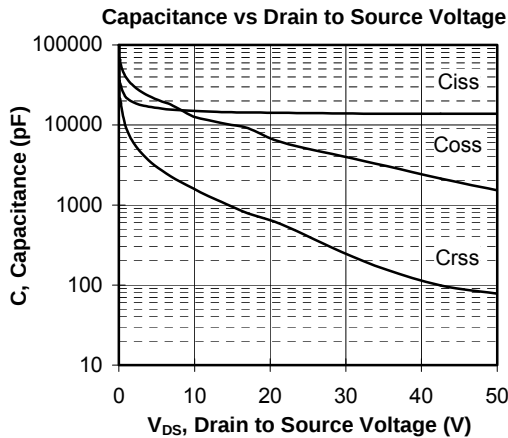
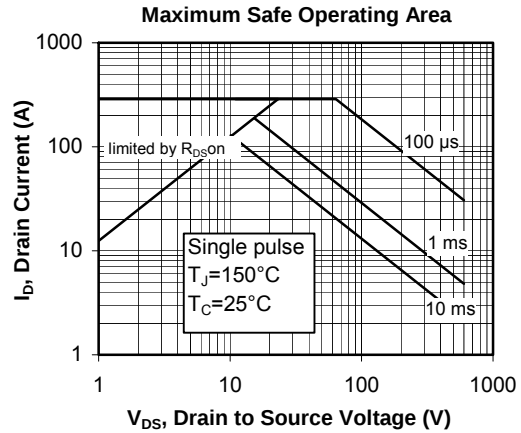
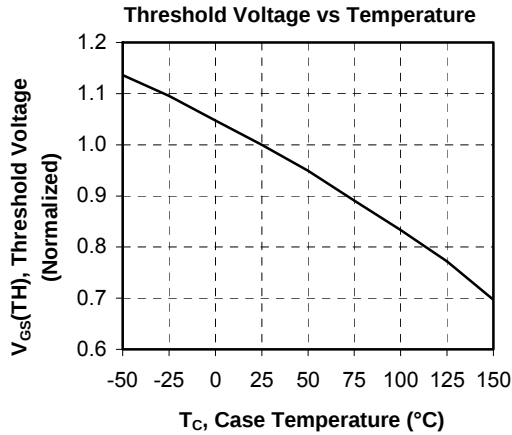
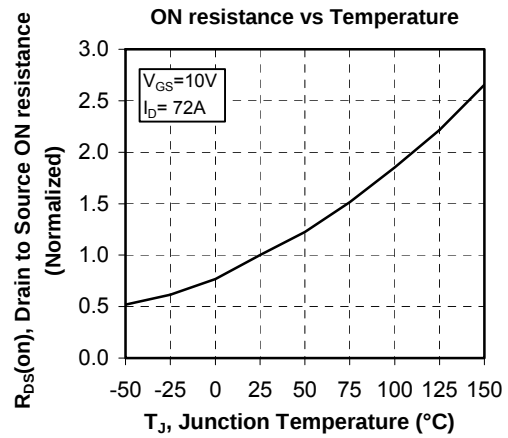
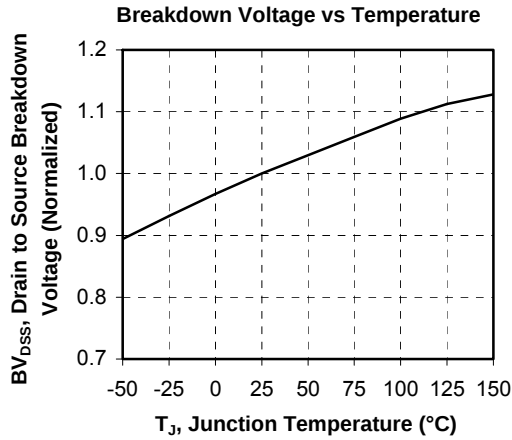
SP3 Package outline (dimensions in mm)

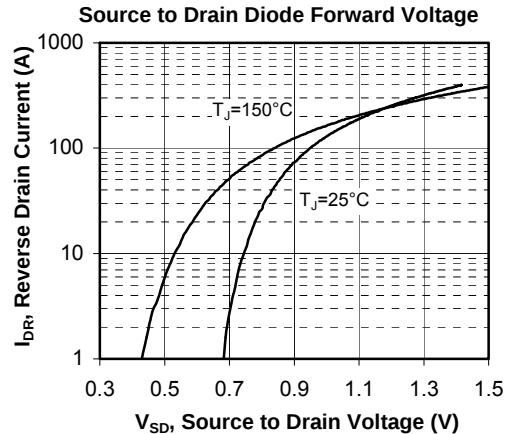
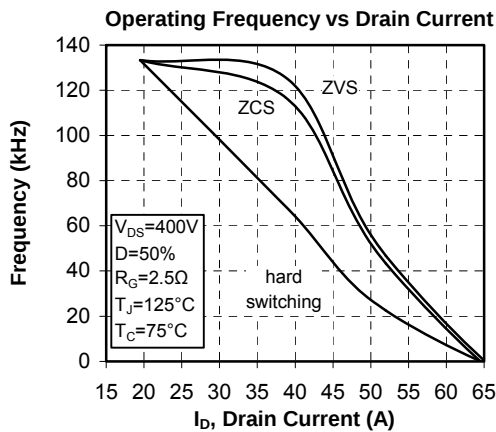
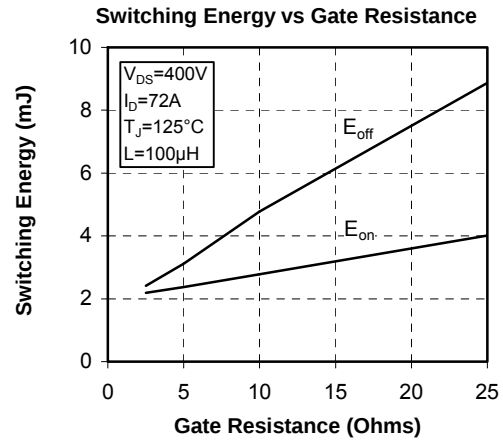
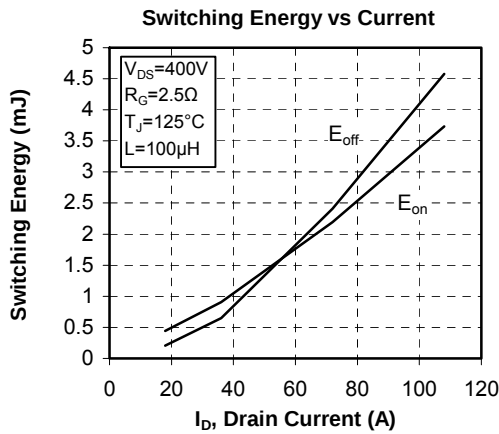
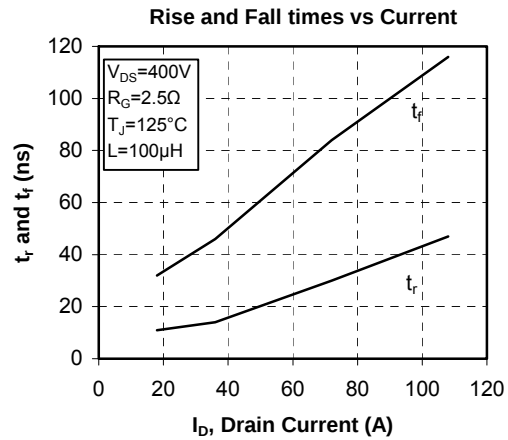
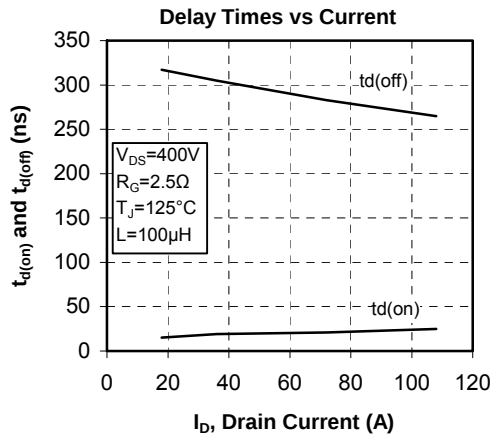


See application note 1901 - Mounting Instructions for SP3 Power Modules on www.microsemi.com

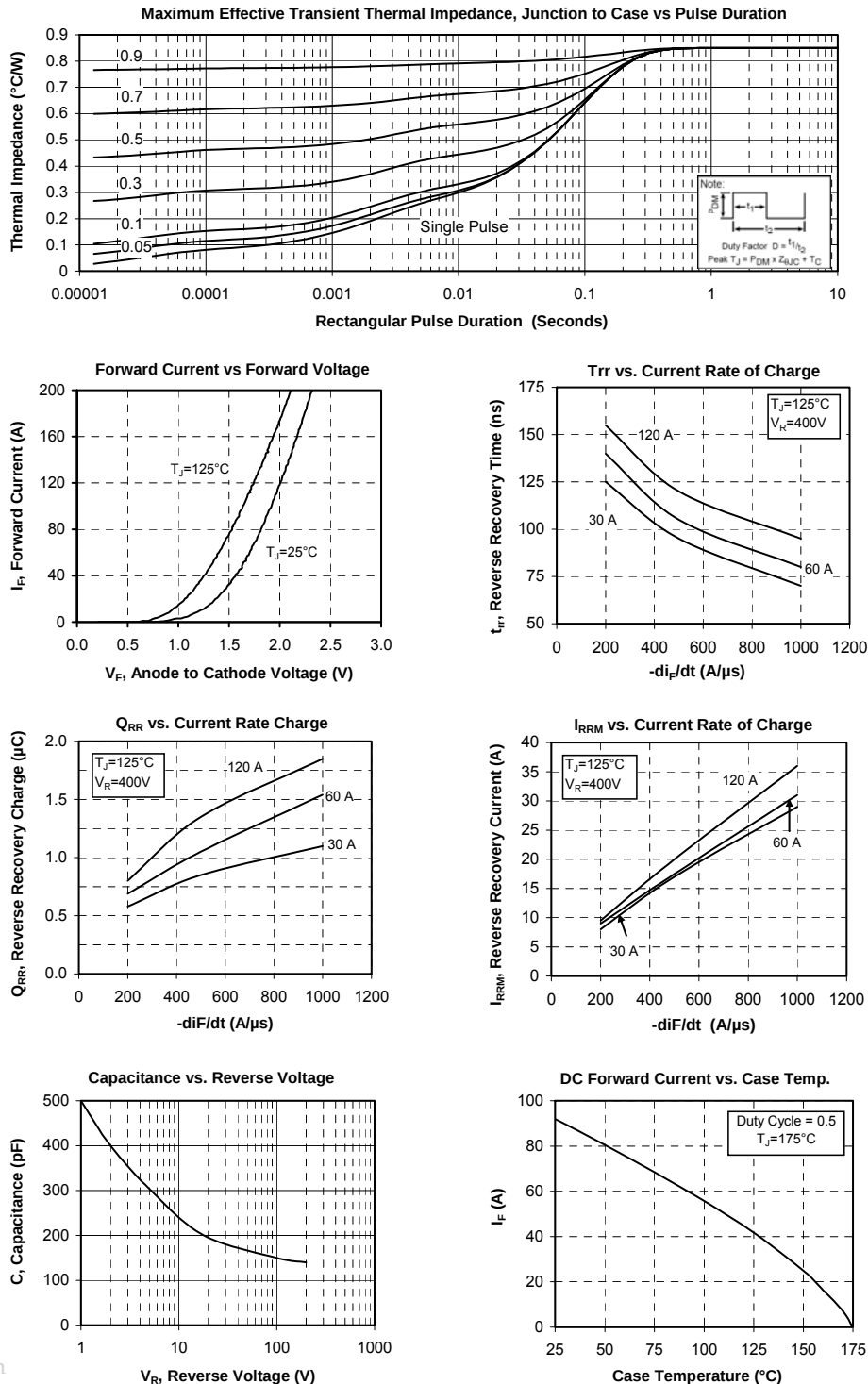
Typical CoolMOS Performance Curve







Typical diode Performance Curve



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